

Type	Description	I_{CEmax} (A)	V_{CEmax} (V)	Power (W)	Gain Bandwidth (MHz)	H_{fe}
2N2646	Unijunction transistor			0.3		
2N2955	Ger. PNP 100mA 40V	0.1	25	0.3		20 - 60
2N3055	Bipolar power NPN 15A 60V	15	60	115	2.5	15 - 120
2N3819	Field effect signal NJFET2-20mA 25V					
2N4959	Bipolar signal PNP 30mA 30V					
2N5192	NPN BJT 4A 80V 40W	4	80	40	2	20 - 80
2N5195	PNP BJT 4A 80V 40W	4	80	40	2	20 - 80
2N5457	Field effect signal NJFET 1.5mA 25v		25	0.31	—	—
2N5458						
2N5461	JFET PCHANNEL DEPLETION		25	0.35	—	—
2N918	Bipolar signal NPN 50mA 30V	0.05	15	0.2	600	20 - 50
BC108	Bipolar signal NPN 200mA 30V	0.2	25	1	150	110 - 800
BC179	Bipolar signal PNP 200mA 30V					
BC547	NPN 200mA 50V 500mW	0.1	45	0.625	150	110 - 800
BC548A	NPN 100mA 30v 625mW to-92	0.1	30	0.625	150	110 - 220
BC548B	NPN 100mA 30v 625mW to-92	0.1	30	0.625	150	200 - 450
BC549	Low noise NPN 100mA 30V 625mW	0.1	30	0.625	250	420 - 800
BC556	PNP 100mA 65V 625mW TO-92 (477)	-0.1	-65	0.625	280	120 - 500
BC557	PNP 100mA 45V 625mW TO-92	-0.1	-45	0.625	320	120 - 800
BC558	PNP 100mA 30V 625mW TO-92	-0.1	-30	0.625	360	120 - 800
BC559	PNP Low noise 100mA 30V to-92	-0.1	-30	0.625	250	180 - 460
BC639	high current NPN	0.5	80	0.625	200	40 - 160
BC640	high current PNP	-0.5	-80	0.625	150	40 - 160
BD139	NPN BJT signal 1.5A 80V 12.5W	1.5	80	8	190	40 - 250
BD140	PNP Bipolar signal 1.5A 80V 12.5W	-1.5	-80	8	160	40 - 250
BFY90	rf npn low power Wide band input					
IRF530	Field effect power..14A 100V	14	100	75	—	—
IRGBC20F	Fast 16A 600V	16	600	60	—	—
MFE131	Dual gate Mos-Fet					
MJ802	NPN TO3 30A 100V	4	80	40	1	100 - 750
MJE2955	PNP BJT 15A 60V 90W	10	60	75	2	20 - 100
MJE3055	NPN BJT 15A 60V 90W	10	60	75	2	21 - 100
MJE340	NPN 1A 300V TO126	0.5	300	20.8		30 - 240
PN100	NPN general purpose medium power	0.5	75		250	80 - 600
PN200	PNP general purpose medium power	-0.5	-60		250	80 - 600
TIP 31	PNP silicon power	-1	-40	30	3	15 - 75